



ABSTRACT

The present invention relates to a film comprising silicon dioxide as the main component, which contains Zr, etc., and a method for forming it by reactive DC sputtering. It makes it possible to form reflection preventive films, alkali barrier films and various multi-layered films such as multi-layered films for anti-iridescent glass, which contain said film comprising silicon dioxide as the main component, by a physical vapor deposition method without breaking a vacuum.